

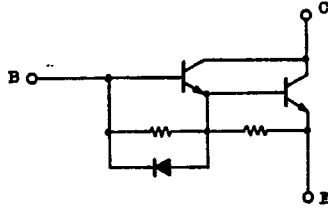
9097250 TOSHIBA (DISCRETE/OPTO)

90D 16230 DT-33-35

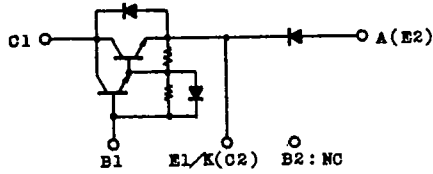


SEMICONDUCTOR
TECHNICAL DATA

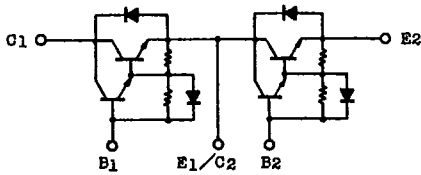
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- MG50G1JL1
- MG50G2CL3
- MG50G2DL1
- MG50G6EL1



MG50G1BL3

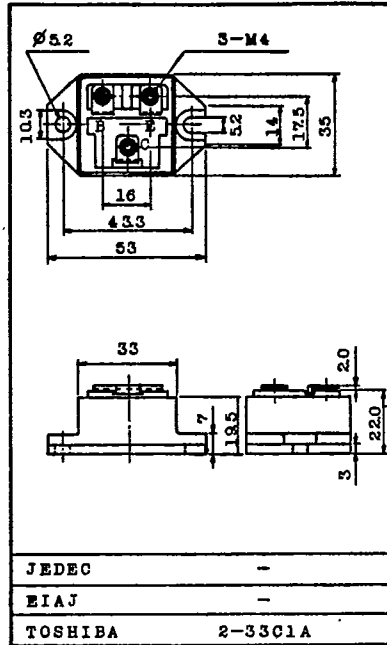


MG50G1JL1

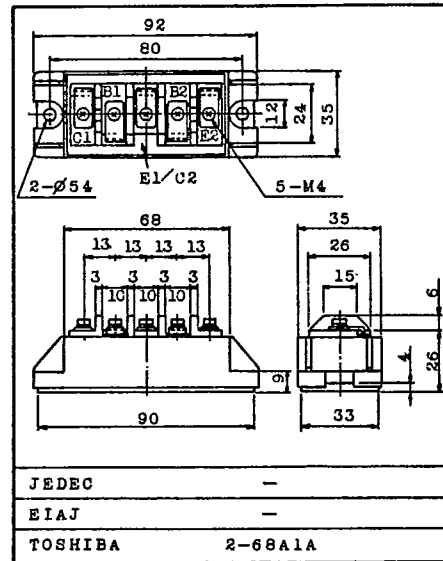


MG50G2CL3

Unit in mm



Weight : 86g



Weight : 210g

TOSHIBA CORPORATION

GT1A2A

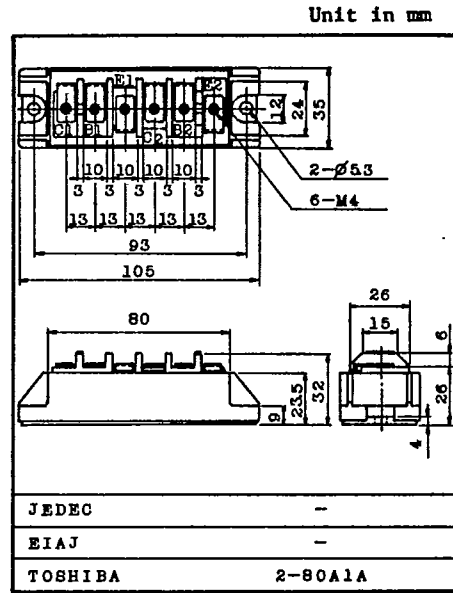
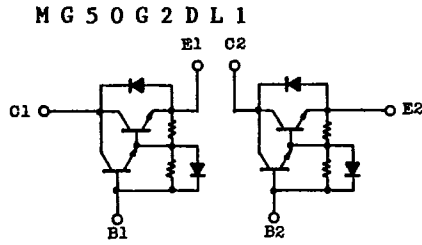
9097250 TOSHIBA (DISCRETE/OPTO)

90D 16231 DT-33-35

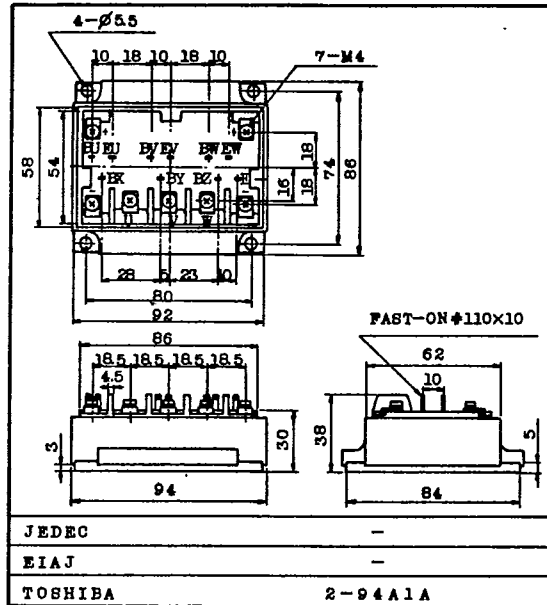
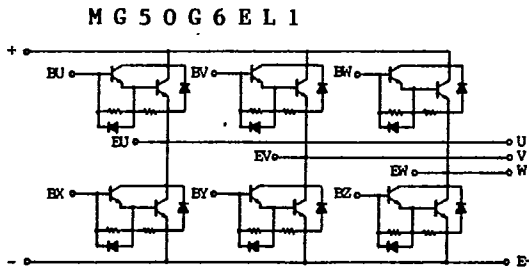


SEMICONDUCTOR
TECHNICAL DATA

- MG50G1BL3
- MG50G1JL1
- MG50G2CL3
- MG50G2DL1
- MG50G6EL1



Weight : 245g



Weight : 600g

TOSHIBA CORPORATION

GT1A2A

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16232 DT-33-35



SEMICONDUCTOR

東芝

TECHNICAL DATA

M G 5 0 G 1 B L 3

M G 5 0 G 1 J L 1

M G 5 0 G 2 C L 3

M G 5 0 G 2 D L 1

M G 5 0 G 6 E L 1

MAXIMUM RATINGS (Ta=25°C)

| CHARACTERISTIC | | SYMBOL | RATING | UNIT |
|---------------------------------------|-----|-----------------------|--------------------|-------|
| Collector-Base Voltage | | V _{CB0} | 600 | V |
| Collector-Emitter Voltage | | V _{CEO} | 600 | V |
| Collector-Emitter Sustaining Voltage | | V _{CEO(SUS)} | 450 | V |
| Emitter-Base Voltage | | V _{EB0} | 6 | V |
| Collector Current | DC | I _C | 50 | A |
| | 1ms | I _C | 100 | A |
| | DC | -I _C | 50 | A |
| Base Current | | I _B | 3 | A |
| Collector Power Dissipation (Tc=25°C) | | P _C | 300 | W |
| Junction Temperature | | T _j | 150 | °C |
| Storage Temperature Range | | T _{stg} | -40~125 | °C |
| Isolation Voltage | | V _{isol} | 2500 (AC 1 Minute) | V |
| Screw Torque (Terminal/Mounting) | | | 20/30 | kg·cm |

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| CHARACTERISTIC | | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|---------------------------------------|--------------|-----------------------|--|------|------|------|------|
| Collector Cut-off Current | | I _{CB0} | V _{CB} =600V, I _E =0 | - | - | 1.0 | mA |
| Emitter Cut-off Current | | I _{EB0} | V _{EB} =6V, I _C =0 | - | - | 200 | mA |
| Collector-Emitter Sustaining Voltage | | V _{CEO(SUS)} | I _C =0.5A, L=40mH | 450 | - | - | V |
| DC Current Gain | | h _{FE} | V _{CE} =5V, I _C =50A | 100 | - | - | |
| Collector-Emitter Saturation Voltage | | V _{CE(sat)} | I _C =50A, I _B =1A | - | - | 2.0 | V |
| Base-Emitter Saturation Voltage | | V _{BE(sat)} | | - | - | 2.5 | V |
| Emitter-Collector Voltage | | V _{ECO} | I _E =50A, I _B =0 | - | - | 1.5 | V |
| Reverse Recovery Time | | t _{rr} | -I _C =50A, V _{EB} =3V, V _{CE} =300V | - | - | 2.0 | μs |
| Switching Time | Turn-on Time | t _{on} | | - | - | 1.0 | μs |
| | Storage Time | t _{stg} | | - | - | 12 | |
| | Fall Time | t _f | | - | - | 2.0 | |
| Thermal Resistance (Junction to Case) | | R _{th(j-c)} | Transistor | - | - | 0.41 | °C/W |
| | | | Diode | - | - | 1.3 | |

TOSHIBA CORPORATION

GT1A2

- 238 -

9097250 TOSHIBA (DISCRETE/OPTO)

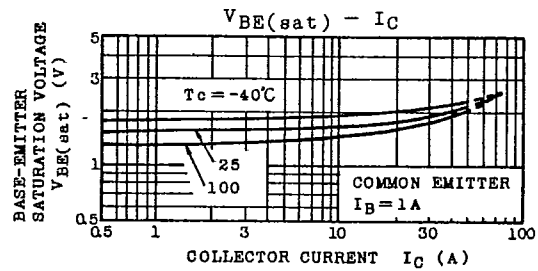
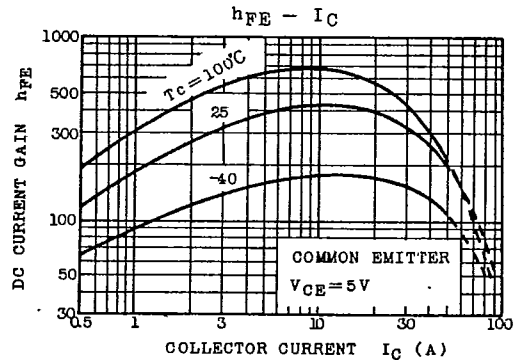
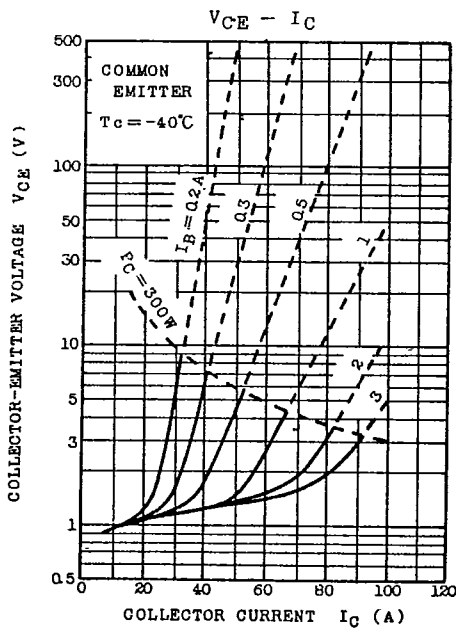
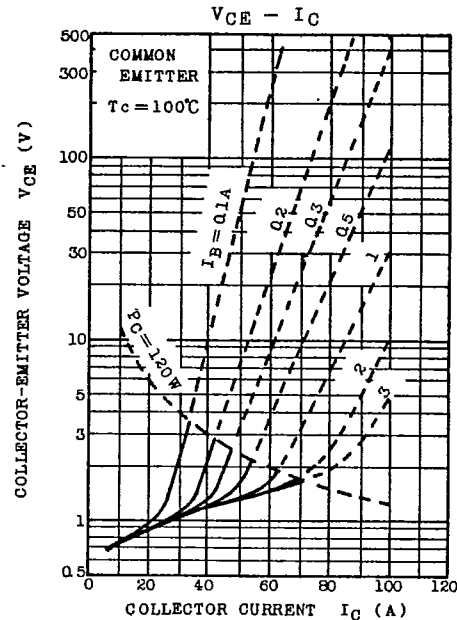
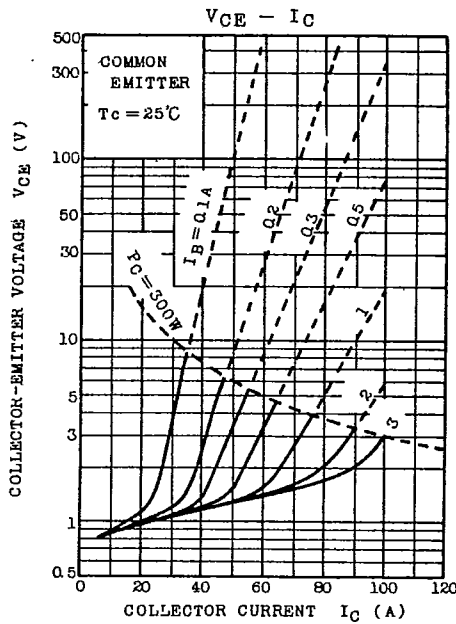
90D 16233 DT-33-35



SEMICONDUCTOR

TECHNICAL DATA

- MG 50 G 1 B L 3
- MG 50 G 1 J L 1
- MG 50 G 2 C L 3
- MG 50 G 2 D L 1
- MG 50 G 6 E L 1



TOSHIBA CORPORATION

GT1A2

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16234

DT-33-35



SEMICONDUCTOR

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TECHNICAL DATA

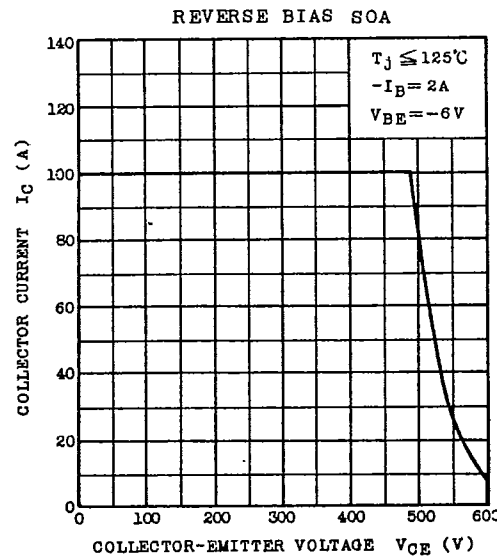
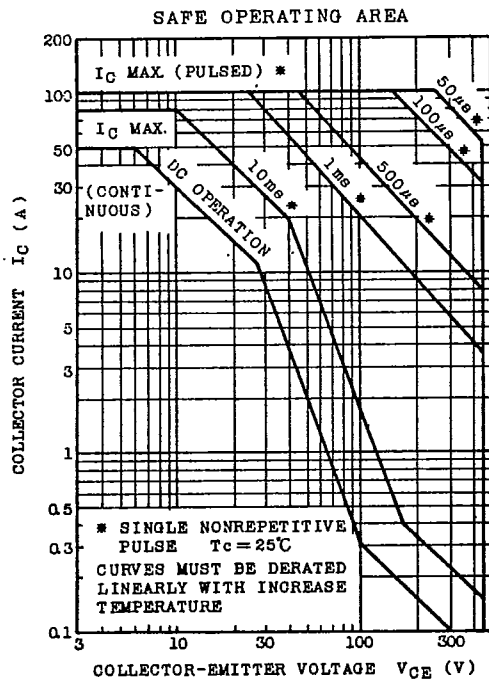
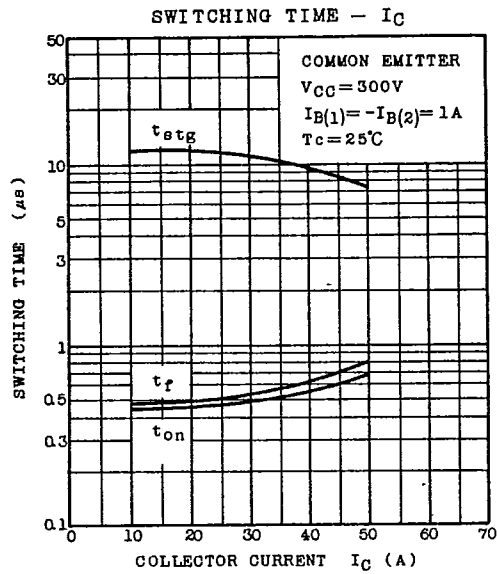
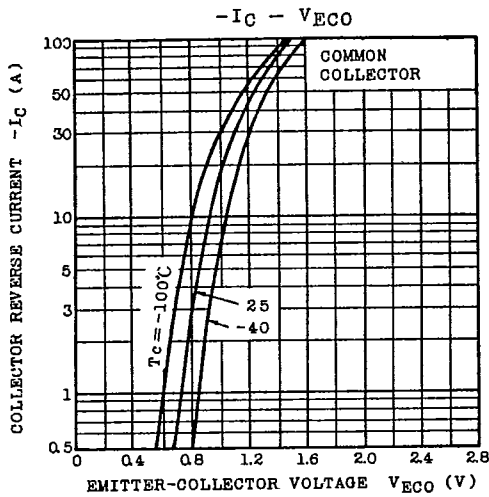
MG50G1BL3

MG50G1JL1

MG50G2CL3

MG50G2DL1

MG50G6EL1



TOSHIBA CORPORATION

GT1A2

9097250 TOSHIBA (DISCRETE/OPTO)

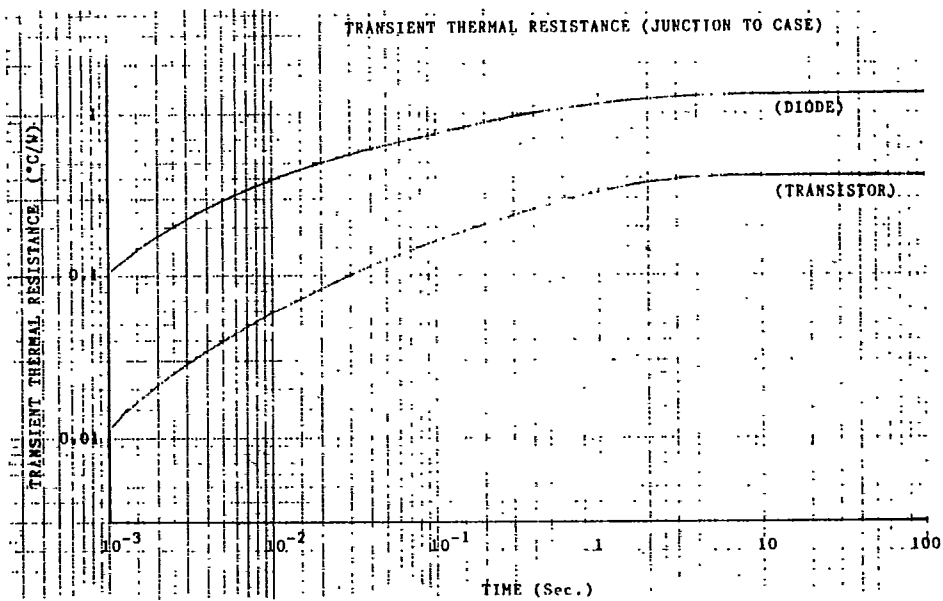
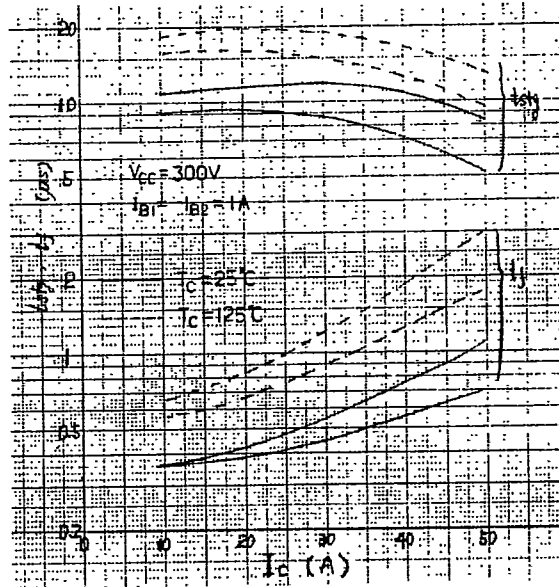
90D 16235 DT-33-35



SEMICONDUCTOR

TECHNICAL DATA

- MG50G1BL3
- MG50G1JL1
- MG50G2CL3
- MG50G2DL1
- MG50G6EL1



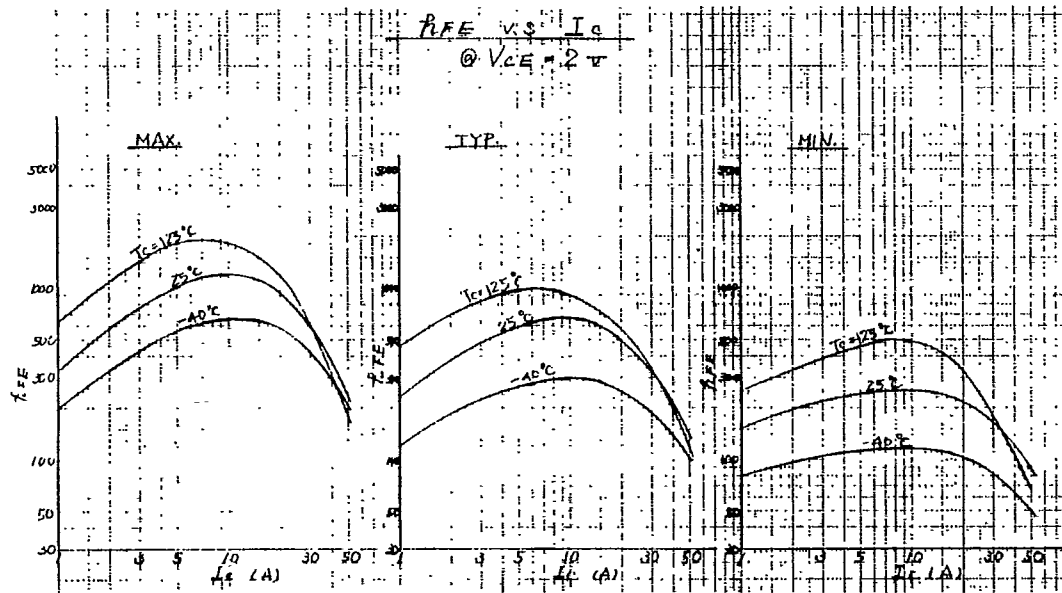
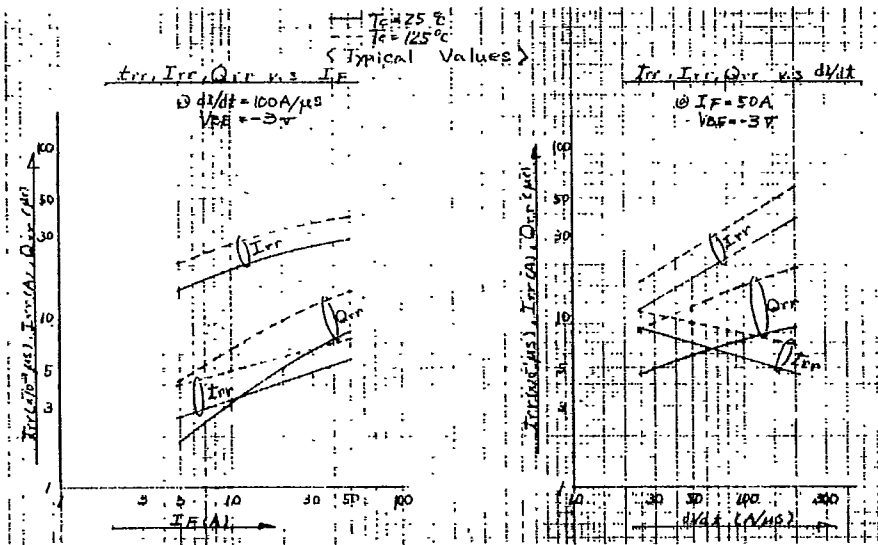
TOSHIBA CORPORATION

GT1A2A



SEMICONDUCTOR
TECHNICAL DATA

- MG50G1BL3
- MG50G1JL1
- MG50G2CL3
- MG50G2DL1
- MG50G6EL1



TOSHIBA CORPORATION

GT1A2A